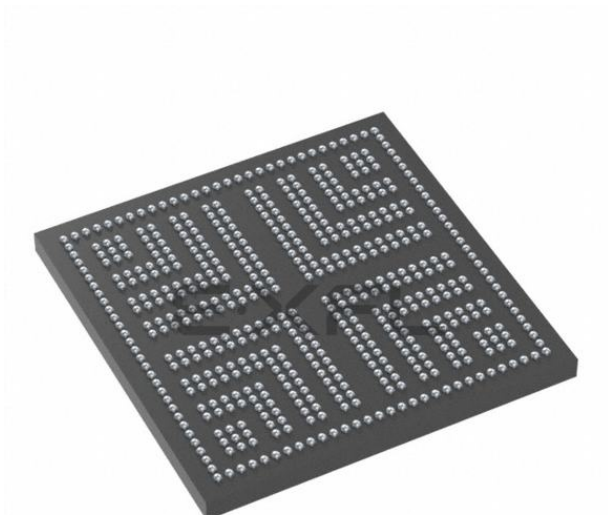




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	192000
Total RAM Bits	13619200
Number of I/O	300
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	536-LFBGA, CSPBGA
Supplier Device Package	536-CSPBGA (16x16)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf200ts-fcsg536i

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2 Overview

This datasheet describes PolarFire® FPGA device characteristics with industrial temperature range (–40 °C to 100 °C T_J) and extended commercial temperature range (0 °C to 100 °C T_J). The devices are provided with a standard speed grade (STD) and a –1 speed grade with higher performance. The FPGA core supply V_{DD} can operate at 1.0 V for lower-power or 1.05 V for higher performance. Similarly, the transceiver core supply V_{DDA} can also operate at 1.0 V or 1.05 V. Users select the core operating voltage while creating the Libero project.

4 Device Offering

The following table lists the PolarFire FPGA device options using the MPF300T as an example. The MPF100T, MPF200T, and MPF500T device densities have identical offerings.

Table 1 • PolarFire FPGA Device Options

Device Options	Extended Commercial 0 °C–100 °C	Industrial –40 °C–100 °C	STD	–1	Transceivers T	Lower Static Power L	Data Security S
MPF300T	Yes	Yes	Yes	Yes	Yes		
MPF300TL	Yes	Yes	Yes		Yes	Yes	
MPF300TS		Yes	Yes	Yes	Yes		Yes
MPF300TLS		Yes	Yes		Yes	Yes	Yes

Note: The following dedicated pins do not support hot socketing: TMS, TDI, TRSTB, DEVRST_N, and FF_EXIT_N. Weak pull-up (as specified in GPIO) is always enabled.

6.3 Input and Output

The following section describes:

- DC I/O levels
- Differential and complementary differential DC I/O levels
- HSIO and GPIO on-die termination specifications
- LVDS specifications

6.3.1 DC Input and Output Levels

The following tables list the DC I/O levels.

Table 12 • DC Input Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{IL} Min (V)	V _{IL} Max (V)	V _{IH} Min (V)	V _{IH} ¹ Max (V)
PCI	3.15	3.3	3.45	−0.3	0.3 x V _{DDI}	0.5 x V _{DDI}	3.45
LVTTL	3.15	3.3	3.45	−0.3	0.8	2	3.45
LVC MOS33	3.15	3.3	3.45	−0.3	0.8	2	3.45
LVC MOS25	2.375	2.5	2.625	−0.3	0.7	1.7	2.625
LVC MOS18	1.71	1.8	1.89	−0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.89
LVC MOS15	1.425	1.5	1.575	−0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.575
LVC MOS12	1.14	1.2	1.26	−0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.26
SSTL25I ²	2.375	2.5	2.625	−0.3	V _{REF} − 0.15	V _{REF} + 0.15	2.625
SSTL25II ²	2.375	2.5	2.625	−0.3	V _{REF} − 0.15	V _{REF} + 0.15	2.625
SSTL18I ²	1.71	1.8	1.89	−0.3	V _{REF} − 0.125	V _{REF} + 0.125	1.89
SSTL18II ²	1.71	1.8	1.89	−0.3	V _{REF} − 0.125	V _{REF} + 0.125	1.89
SSTL15I	1.425	1.5	1.575	−0.3	V _{REF} − 0.1	V _{REF} + 0.1	1.575
SSTL15II	1.425	1.5	1.575	−0.3	V _{REF} − 0.1	V _{REF} + 0.1	1.575

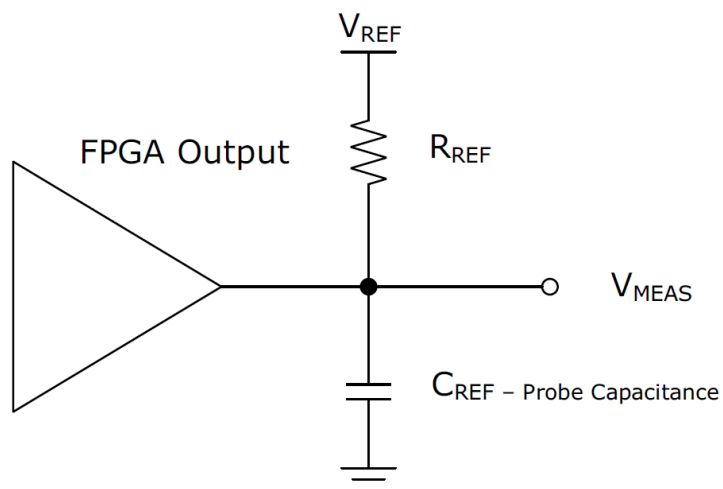
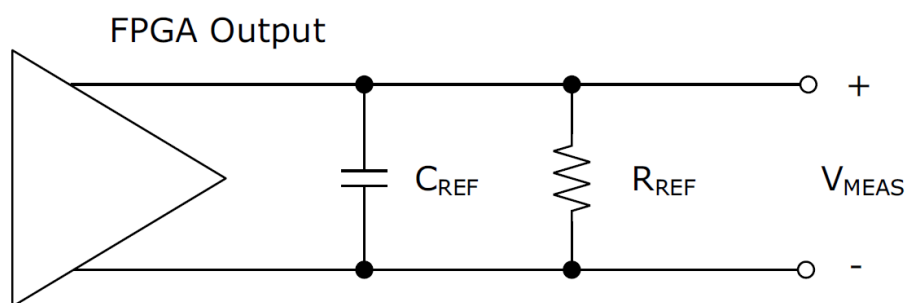
Table 13 • DC Output Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
PCI ¹	3.15	3.3	3.45		0.1 x V _{DDI}	0.9 x V _{DDI}		1.5	0.5
LVTTL	3.15	3.3	3.45		0.4	2.4			
LVC MOS33	3.15	3.3	3.45		0.4	V _{DDI} – 0.4			
LVC MOS25	2.375	2.5	2.625		0.4	V _{DDI} – 0.4			
LVC MOS18	1.71	1.8	1.89		0.45	V _{DDI} – 0.45			
LVC MOS15	1.425	1.5	1.575		0.25 x V _{DDI}	0.75 x V _{DDI}			
LVC MOS12	1.14	1.2	1.26		0.25 x V _{DDI}	0.75 x V _{DDI}			
SSTL25I ³	2.375	2.5	2.625		V _{TT} – 0.608	V _{TT} + 0.608		8.1	8.1
SSTL25II ³	2.375	2.5	2.625		V _{TT} – 0.810	V _{TT} + 0.810		16.2	16.2
SSTL18I ³	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603		6.7	6.7
SSTL18II ³	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603		13.4	13.4
SSTL15I ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL15II ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34
SSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34
HSTL15I	1.425	1.5	1.575		0.4	V _{DDI} – 0.4		8	8
HSTL15II	1.425	1.5	1.575		0.4	V _{DDI} – 0.4		16	16

Standard	Description	V_I^1	V_H^1	V_{ID}^2	V_{ICM}^2	$V_{MEAS}^{3,4}$	$V_{REF}^{1,5}$	Unit
HSUL18I	HSUL 1.8 V Class I	$V_{REF} -$ 0.54	$V_{REF} +$ 0.54			V_{REF}	0.90	V
HSUL18II	HSUL 1.8 V Class II	$V_{REF} -$ 0.54	$V_{REF} +$ 0.54			V_{REF}	0.90	V
HSUL12	HSUL 1.2 V	$V_{REF} -$.22	$V_{REF} +$.22			V_{REF}	0.60	V
POD12I	Pseudo open drain (POD) logic 1.2 V Class I	$V_{REF} -$.15	$V_{REF} +$.15			V_{REF}	0.84	V
POD12II	POD 1.2 V Class II	$V_{REF} -$.15	$V_{REF} +$.15			V_{REF}	0.84	V
LVDS33	Low-voltage differential signaling (LVDS) 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
LVDS25	LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
LVDS18	LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
RSDS33	RSDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
RSDS25	RSDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
RSDS18	RSDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS33	Mini-LVDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS25	Mini-LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS18	Mini-LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
SUBLVDS33	Sub-LVDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
SUBLVDS25	Sub-LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
SUBLVDS18	Sub-LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
PPDS33	Point-to-point differential signaling 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
PPDS25	PPDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
PPDS18	PPDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
SLVS33	Scalable low- voltage signaling 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.200	0		V

Standard	Description	R _{REF} (Ω)	C _{REF} (pF)	V _{MEAS} (V)	V _{REF} (V)
SSTL18I	SSTL 1.8 V Class I	50	0	V _{REF}	0.9
SSTL18II	SSTL 1.8 V Class II	50	0	V _{REF}	0.9
SSTL15I	SSTL 1.5 V Class I	50	0	V _{REF}	0.75
SSTL15II	SSTL 1.5 V Class II	50	0	V _{REF}	0.75
SSTL135I	SSTL 1.35 V Class I	50	0	V _{REF}	0.675
SSTL135II	SSTL 1.35 V Class II	50	0	V _{REF}	0.675
HSTL15I	High-speed transceiver logic (HSTL) 1.5 V Class I	50	0	V _{REF}	0.75
HSTL15II	HSTL 1.5 V Class II	50	0	V _{REF}	0.75
HSTL135I	HSTL 1.35 V Class I	50	0	V _{REF}	0.675
HSTL135II	HSTL 1.35 V Class II	50	0	V _{REF}	0.675
HSTL12	HSTL 1.2 V	50	0	V _{REF}	0.6
HSUL18I	High-speed unterminated logic 1.8 V Class I	50	0	V _{REF}	0.9
HSUL18II	HSUL 1.8 V Class II	50	0	V _{REF}	0.9
HSUL12	HSUL 1.2 V	50	0	V _{REF}	0.6
POD12I	Pseudo open drain (POD) logic 1.2 V Class I	50	0	V _{REF}	0.84
POD12II	POD 1.2 V Class II	50	0	V _{REF}	0.84
LVDS33	LVDS 3.3 V	100	0	0 ¹	0
LVDS25	LVDS 2.5 V	100	0	0 ¹	0
LVDS18	LVDS 1.8 V	100	0	0 ¹	0
RSDS33	Reduced swing differential signaling 3.3 V	100	0	0 ¹	0
RSDS25	RSDS 2.5 V	100	0	0 ¹	0
RSDS18	RSDS 1.8 V	100	0	0 ¹	0
MINILVDS33	Mini-LVDS 3.3 V	100	0	0 ¹	0
MINILVDS25	Mini-LVDS 2.5 V	100	0	0 ¹	0
SUBLVDS33	Sub-LVDS 3.3 V	100	0	0 ¹	0
SUBLVDS25	Sub-LVDS 2.5 V	100	0	0 ¹	0
PPDS33	Point-to-point differential signaling 3.3 V	100	0	0 ¹	0
PPDS25	PPDS 2.5 V	100	0	0 ¹	0
BUSLVDS25	Bus LVDS	100	0	0 ¹	0
MLVDS25	Multipoint LVDS 2.5 V	100	0	0 ¹	0
LVPECLE33	Low-voltage positive emitter-coupled logic	100	0	0 ¹	0
MIPIE25	Mobile industry processor interface 2.5 V	100	0	0 ¹	0

1. The value given is the differential output voltage.

Figure 1 • Output Delay Measurement—Single-Ended Test Setup

Figure 2 • Output Delay Measurement—Differential Test Setup


7.1.3 Input Buffer Speed

The following tables provide information about input buffer speed.

Table 24 • HSIO Maximum Input Buffer Speed

Standard	STD	-1	Unit
LVDS18	1250	1250	Mbps
RDS18	800	800	Mbps
MINILVDS18	800	800	Mbps
SUBLVDS18	800	800	Mbps
PPDS18	800	800	Mbps
SLVS18	800	800	Mbps
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps

Standard	STD	–1	Unit
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL12	1066	1333	Mbps
HSTL12	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMS18 (12 mA)	500	500	Mbps
LVCMS15 (10 mA)	500	500	Mbps
LVCMS12 (8 mA)	300	300	Mbps

1. Performance is achieved with $V_{ID} \geq 200$ mV.

Table 25 • GPIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS25/LVDS33/LCMDS25/LCMDS33	1250	1600	Mbps
RSDS25/RSDS33	800	800	Mbps
MINILVDS25/MINILVDS33	800	800	Mbps
SUBLVDS25/SUBLVDS33	800	800	Mbps
PPDS25/PPDS33	800	800	Mbps
SLVS25/SLVS33	800	800	Mbps
SLVSE15	800	800	Mbps
HCSL25/HCSL33	800	800	Mbps
BUSLVDSE25	800	800	Mbps
MLVDSE25	800	800	Mbps
LVPECL33	800	800	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
HSTL15I	800	900	Mbps
HSTL15II	800	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
PCI	500	500	Mbps
LVTTTL33 (20 mA)	500	500	Mbps
LVCMS33 (20 mA)	500	500	Mbps
LVCMS25 (16 mA)	500	500	Mbps

Standard	STD	–1	Unit
LVC MOS12 (8 mA)	250	300	Mbps

Table 27 • GPIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
LVDS25/LCMDS25	1250	1250	Mbps
LVDS33/LCMDS33	1250	1600	Mbps
RSDS25	800	800	Mbps
MINILVDS25	800	800	Mbps
SUBLVDS25	800	800	Mbps
PPDS25	800	800	Mbps
SLVSE15	500	500	Mbps
BUSLVDS25	500	500	Mbps
MLVDS25	500	500	Mbps
LVPECL33	500	500	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL25I (differential)	800	800	Mbps
SSTL25II (differential)	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL18I (differential)	800	800	Mbps
SSTL18II (differential)	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
SSTL15I (differential)	800	1066	Mbps
SSTL15II (differential)	800	1066	Mbps
HSTL15I	900	900	Mbps
HSTL15II	900	900	Mbps
HSTL15I (differential)	900	900	Mbps
HSTL15II (differential)	900	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18I (differential)	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
PCI	500	500	Mbps
LVTTTL33 (20 mA)	500	500	Mbps
LVC MOS33 (20 mA)	500	500	Mbps
LVC MOS25 (16 mA)	500	500	Mbps
LVC MOS18 (12 mA)	500	500	Mbps
LVC MOS15 (10 mA)	500	500	Mbps
LVC MOS12 (8 mA)	250	300	Mbps
MIPIE25	500	500	Mbps

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Clock-to-Data Condition
F _{MAX} 4:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 8:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 2:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 4:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
F _{MAX} 8:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Table 32 • I/O Digital Transmit Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output F _{MAX}	TX_SDR_G_A	Tx SDR							MHz	From a global clock source, aligned ¹
	TX_SDR_G_C	Tx SDR							MHz	From a global clock source, centered ¹

1. A centered clock-to-data interface can be created with a negedge launch of the data.

Table 33 • I/O Digital Transmit Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output F _{MAX}	TX_DDR_G_A	Tx DDR			335			335	MHz	From a global clock source, aligned
	TX_DDR_G_C	Tx DDR			335			335	MHz	From a global clock source, centered
	TX_DDR_L_A	Tx DDR			250			250	MHz	From a lane clock source, aligned
	TX_DDR_L_C	Tx DDR			250			250	MHz	From a lane clock source, centered
Output F _{MAX} 2:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output F _{MAX} 4:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output F _{MAX} 8:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned

Table 60 • 10GbE (RXAU)

	Data Rate	Min	Max	Unit
Total transmit jitter	6.25 Gbps			UI
Receiver jitter tolerance	6.25 Gbps			UI

7.5.4**1GbE (1000BASE-T)**

The following table describes 1GbE (1000BASE-T).

Table 61 • 1GbE (1000BASE-T)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

The following table describes 1GbE (1000BASE-X).

Table 62 • 1GbE (1000BASE-X)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

7.5.5**SGMII and QSGMII**

The following table describes SGMII.

Table 63 • SGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps		0.24	UI
Receiver jitter tolerance	1.25 Gbps	0.749		UI

The following table describes QSGMII.

Table 64 • QSGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps		0.3	UI
Receiver jitter tolerance	5.0 Gbps	0.65		UI

7.5.6**SDI**

The following table describes SDI.

Table 65 • SDI

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter				UI
Receiver jitter tolerance				UI

7.6.3 FPGA Bitstream Sizes

The following table describes FPGA bitstream sizes.

Table 72 • Initialization Client Sizes

Device	Plaintext	Ciphertext
MPF100T, TL, TS, TLS		
MPF200T, TL, TS, TLS	2916 KB	3006 KB
MPF300T, TL, TS, TLS	4265 KB	4403 KB
MPF500T, TL, TS, TLS		

Note: Worst case initializing all fabric LSRAM, USRAM, and UPROM.

Table 73 • Bitstream Sizes

File	Devices	FPGA	Security	SNVM (all pages)	FPGA+ SNVM	FPGA+ Sec	SNVM+ Sec	FPGA+ SNVM+ Sec
SPI	MPF100T, TL, TS, TLS							
DAT	MPF100T, TL, TS, TLS							
SPI	MPF200T, TL, TS, TLS	5.9 MB	3.4 KB	59.7 KB	5.9 MB	5.9 MB	62.2 KB	6.0 MB
DAT	MPF200T, TL, TS, TLS	5.9 MB	7.3 KB	61.2 KB	6.0 MB	5.9 MB	66.3 KB	6.0 MB
SPI	MPF300T, TL, TS, TLS	9.3 MB	3.5 KB	59.7 KB	9.6 MB	9.5 MB	62.2 KB	9.6 MB
DAT	MPF300T, TL, TS, TLS	9.3 MB	7.6 KB	61.2 KB	9.6 MB	9.5 MB	66.3 KB	9.6 MB
SPI	MPF500T, TL, TS, TLS							
DAT	MPF500T, TL, TS, TLS							

7.6.4 Digest Cycles

Digests verify the integrity of the programmed non-volatile data. Digests are a cryptographic hash of various data areas. Any digest that reports back an error raises the digest tamper flag.

Table 74 • Maximum Number of Digest Cycles

Retention Since Programmed (N = Number Digests During that Time) ¹										
Digest T _i	Storage and Operating T _j	N ≤300	N = 500	N = 1000	N = 1500	N = 2000	N = 4000	N = 6000	Unit	Retention
–40 to 100	–40 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
–40 to 100	0 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
–40 to 85	–40 to 85	20 × LF	20 × LF	20 × LF	20 × LF	16 × LF	8 × LF	4 × LF	°C	Years
–40 to 55	–40 to 55	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	°C	Years

1. LF = Lifetime factor as defined by the number of programming cycles the device has seen under the conditions listed in the following table.

Parameter	Devices	Typ	Max	Unit
UFS UPERM digest run time	MPF100T, TL, TS, TLS			μs
	MPF200T, TL, TS, TLS	33.2	34.9	μs
	MPF300T, TL, TS, TLS	33.2	34.9	μs
	MPF500T, TL, TS, TLS			μs
Factory digest run time	MPF100T, TL, TS, TLS			μs
	MPF200T, TL, TS, TLS	493.6	510.1	μs
	MPF300T, TL, TS, TLS	493.6	510.1	μs
	MPF500T, TL, TS, TLS			μs

1. The entire sNVM is used as ROM.
2. Valid for user key 0 through 6.

Note: These times do not include the power-up to functional timing overhead when using digest checks on power-up.

7.6.6 Zeroization Time

The following tables describe zeroization time. A zeroization operation is counted as one programming cycle.

Table 77 • Zeroization Times for MPF100T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1, 4}			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 78 • Zeroization Times for MPF200T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (recoverable) ^{1,3}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1,4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1,2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1,3}			s	Full scrubbing
Time to scrub the fabric data PNVM data (non-recoverable) ^{1,4}			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 79 • Zeroization Times for MPF300T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1,2}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1,3}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1,4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1,2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1,3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1,4}			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 80 • Zeroization Times for MPF500T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1,2}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1,3}			ms	One iteration of scrubbing

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Authenticated text read		113.25	114.02	118.5	μs	
Authenticated and decrypted text read		159.59	160.53	166.5	μs	

Notes:

- Page size= 252 bytes (non-authenticated), 236 bytes (authenticated).
- Only page reads and writes allowed.
- T_{PUF_OVHD} is an additional time that occurs on the first R/W, after cold or warm boot, to sNVM using authenticated or authenticated and encrypted text.

7.6.10 Secure NVM Programming Cycles

The following table describes secure NVM programming cycles.

Table 86 • sNVM Programming Cycles vs. Retention Characteristics

Programming Temperature	Programming Cycles per Page, Max	Programming Cycles per Block, Max	Retention Years
–40 °C to 100 °C	10,000	100,000	20
–40 °C to 85 °C	10,000	100,000	20
–40 °C to 55 °C	10,000	100,000	20

Note: Page size = 128 bytes. Block size = 56 KBytes.

7.7 System Services

This section describes system switching and throughput characteristics.

7.7.1 System Services Throughput Characteristics

The following table describes system services throughput characteristics.

Table 87 • System Services Throughput Characteristics

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Serial number	T _{Serial}	00H	65	67	μs	
User code	T _{User}	01H	0.8	1.05	μs	
Design information	T _{Design}	02H	2.4	2.7	μs	
Device certificate	T _{Cert}	03H	255	271	ms	
Read digests	T _{digest_read}	04H	201	215	μs	
Query security locks	T _{sec_Query}	05H	15	17	μs	
Read debug information	T _{Rd_debug}	06H	34	38	μs	
Reserved		07H–0FH				
Secure NVM write plain text	T _{sNVM_Wr_Plain}	10H				Note 1
Secure NVM write authenticated plain text	T _{sNVM_Wr_Auth}	11H				Note 1
Secure NVM write authenticated cipher text	T _{sNVM_Wr_Cipher}	12H				Note 1
Reserved		13H–17H				

Parameter	Symbol	Typ	Max	Unit
Time from negation of RESPONSE to all I/Os re-enabled	T _{CLR_IO_DISABLE}	28	38	μs
Time from triggering the response to security locked	T _{LOCKDOWN}			ns
Time from negation of RESPONSE to earlier security unlock condition	T _{CLR_LOCKDOWN}			ns
Time from triggering the response to device enters RESET	T _{tr_RESET}	11.7	14	μs
Time from triggering the response to start of zeroization	T _{tr_ZEROLISE}	7.4	8.2	ms

7.8.5 System Controller Suspend Switching Characteristics

The following table describes the characteristics of system controller suspend switching.

Table 95 • System Controller Suspend Entry and Exit Characteristics

Parameter	Symbol	Definition	Typ	Max	Unit
Time from TRSTb falling edge to SUSPEND_EN signal assertion	T _{suspend_tr} ^{1,2}	Suspend entry time from TRST_N assertion	42	44	ns
Time from TRSTb rising edge to ACTIVE signal assertion	T _{suspend_exit}	Suspend exit time from TRST_N negation	361	372	ns

1. ACTIVE indicates that the system controller is inactive or active regardless of the state of SUSPEND_EN.
2. ACTIVE signal must never be asserted with SUSPEND_EN is asserted.

7.8.6 Dynamic Reconfiguration Interface

The following table provides interface timing information for the DRI, which is an embedded APB slave interface within the FPGA fabric that does not use FPGA resources.

Table 96 • Dynamic Reconfiguration Interface Timing Characteristics

Parameter	Symbol	Max	Unit
PCLK frequency	F _{PD_PCLK}	200	MHz

7.9 Power-Up to Functional Timing

Microsemi non-volatile FPGA technology offers the fastest boot-time of any mid-range FPGA in the market. The following tables describes both cold-boot (from power-on) and warm-boot (assertion of DEVRST_N pin or assertion of reset from the tamper macro) timing. The power-up diagrams assume all power supplies to the device are stable.

7.9.1 Power-On (Cold) Reset Initialization Sequence

The following cold reset timing diagram shows the initialization sequencing of the device.

Table 104 • Flash*Freeze

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from Flash*Freeze entry command to the Flash*Freeze state	T _{FF_ENTRY}		59		μs	
The time from Flash*Freeze exit pin assertion to fabric operational state	T _{FF_FABRIC_UP}		133		μs	
The time from Flash*Freeze exit pin assertion to I/Os operational	T _{FF_IO_ACTIVE}		143		μs	

7.10 Dedicated Pins

The following section describes the dedicated pins.

7.10.1 JTAG Switching Characteristics

The following table describes characteristics of JTAG switching.

Table 105 • JTAG Electrical Characteristics

Symbol	Description	Min	Typ	Max	Unit	Condition
T _{DISU}	TDI input setup time	0.0			ns	
T _{DIHD}	TDI input hold time	2.0			ns	
T _{TMSSU}	TMS input setup time	1.5			ns	
T _{TMSHD}	TMS input hold time	1.5			ns	
F _{TCK}	TCK frequency			25	MHz	
T _{TCKDC}	TCK duty cycle	40		60	%	
T _{TDOCQ}	TDO clock to Q out			8.4	ns	C _{LOAD} = 40 pf
T _{TRSTBCQ}	TRSTB clock to Q out			23.5	ns	C _{LOAD} = 40 pf
T _{TRSTBPW}	TRSTB min pulse width	50			ns	
T _{TRSTBREM}	TRSTB removal time	0.0			ns	
T _{TRSTBREC}	TRSTB recovery time	12.0			ns	
C _{INTDI}	TDI input pin capacitance			5.3	pf	
C _{INTMS}	TMS input pin capacitance			5.3	pf	
C _{INTCK}	TCK input pin capacitance			5.3	pf	
C _{INTTRSTB}	TRSTB input pin capacitance			5.3	pf	

7.10.2 SPI Switching Characteristics

The following tables describe characteristics of SPI switching.

Table 106 • SPI Master Mode (PolarFire Master) During Programming

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F _{MSCK}			20	MHz	

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